

NPN SILICON GERMANIUM RF TRANSISTOR NESG2031M16

NPN SIGE RF TRANSISTOR FOR LOW NOISE, HIGH-GAIN AMPLIFICATION 6-PIN LEAD-LESS MINIMOLD (M16, 1208 PKG)

FEATURES

- The device is an ideal choice for low noise, high-gain amplification NF = 0.8 dB TYP., G_a = 17.0 dB TYP. @ VcE = 2 V, Ic = 5 mA, f = 2 GHz
 - NF = 1.3 dB TYP., G_a = 10.0 dB TYP. @ V_{CE} = 2 V, I_C = 5 mA, f = 5.2 GHz
- Maximum stable power gain: MSG = 21.5 dB TYP. @ VcE = 3 V, Ic = 20 mA, f = 2 GHz
- High breakdown voltage technology for SiGe Tr. adopted: VcEo (absolute maximum ratings) = 5.0 V
- 6-pin lead-less minimold (M16, 1208 PKG)

<R> ORDERING INFORMATION

Part Number	Order Number	Package	Quantity	Supplying Form
NESG2031M16	NESG2031M16-A	6-pin lead-less minimold (M16, 1208 PKG)	50 pcs (Non reel)	• 8 mm wide embossed taping • Pin 1 (Collector), Pin 6 (Emitter) face the
NESG2031M16-T3	NESG2031M16-T3-A	(Pb-Free)	10 kpcs/reel	perforation side of the tape

Remark To order evaluation samples, please contact your nearby sales office. Unit sample quantity is 50 pcs.

ABSOLUTE MAXIMUM RATINGS (TA = +25°C)

Parameter	Symbol	Ratings	Unit
Collector to Base Voltage	Vсво	13.0	V
Collector to Emitter Voltage	Vceo	5.0	V
Emitter to Base Voltage	VEBO	1.5	V
Collector Current	lc	35	mA
Total Power Dissipation	P _{tot} Note	175	mW
Junction Temperature	Tj	150	°C
Storage Temperature	T _{stg}	-65 to +150	°C

Note Mounted on 1.08 cm² × 1.0 mm (t) glass epoxy PCB

Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

Document No. PU10394EJ03V0DS (3rd edition) Date Published September 2009 NS

ELECTRICAL CHARACTERISTICS (TA = +25°C)

Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
DC Characteristics						
Collector Cut-off Current	Ісво	Vcb = 5 V, IE = 0 mA	-	-	100	nA
Emitter Cut-off Current	Ієво	VEB = 1 V, Ic = 0 mA	-	-	100	nA
DC Current Gain	hfe Note 1	Vce = 2 V, Ic = 5 mA	130	190	260	-
RF Characteristics						
Gain Bandwidth Product	f⊤	Vce = 3 V, Ic = 20 mA, f = 2 GHz	20	25	-	GHz
Insertion Power Gain	S _{21e} ²	Vce = 3 V, Ic = 20 mA, f = 2 GHz	16.0	18.0	-	dB
Noise Figure (1)	NF	$\label{eq:Vce} \begin{array}{l} \text{Vce} = 2 \text{ V, Ic} = 5 \text{ mA, f} = 2 \text{ GHz,} \\ \text{Zs} = \text{Zsopt, ZL} = \text{ZLopt} \end{array}$	-	0.8	1.1	dB
Noise Figure (2)	NF	$\label{eq:Vce} \begin{split} &\text{Vce} = 2 \text{ V, Ic} = 5 \text{ mA, f} = 5.2 \text{ GHz,} \\ &\text{Zs} = Z_{\text{Sopt}}, \text{ ZL} = Z_{\text{Lopt}} \end{split}$	-	1.3	-	dB
Associated Gain (1)	Ga	$\label{eq:Vce} \begin{array}{l} \text{Vce} = 2 \text{ V, Ic} = 5 \text{ mA, f} = 2 \text{ GHz,} \\ \text{Zs} = \text{Zsopt, ZL} = \text{ZLopt} \end{array}$	15.0	17.0	-	dB
Associated Gain (2)	Ga	$\label{eq:Vce} \begin{split} &\text{Vce} = 2 \text{ V, Ic} = 5 \text{ mA, f} = 5.2 \text{ GHz,} \\ &\text{Zs} = Z_{\text{Sopt}}, \text{ ZL} = Z_{\text{Lopt}} \end{split}$	=	10.0	-	dB
Reverse Transfer Capacitance	Cre Note 2	Vсв = 2 V, IE = 0 mA, f = 1 MHz	=	0.15	0.25	pF
Maximum Stable Power Gain	MSG Note	VcE = 3 V, Ic = 20 mA, f = 2 GHz	19.0	21.5	-	dB
Gain 1 dB Compression Output Power	Po (1 dB)	$V_{CE} = 3 \text{ V}, \text{ Ic (set)} = 20 \text{ mA (RF OFF)},$ $f = 2 \text{ GHz}, \text{ Zs} = Z_{Sopt}, \text{ ZL} = Z_{Lopt}$	-	13	-	dBm
Output 3rd Order Intercept Point	OIP ₃	$\begin{split} &\text{Vce} = 3 \text{ V, Ic } (\text{set}) = 20 \text{ mA } (\text{RF OFF}), \\ &\text{f} = 2 \text{ GHz, Zs} = Z_{\text{Sopt}}, Z_{\text{L}} = Z_{\text{Lopt}} \end{split}$	=	23	=	dBm

Notes 1. Pulse measurement: PW $\leq 350~\mu\text{s},~\text{Duty Cycle} \leq 2\%$

2. Collector to base capacitance when the emitter grounded

3. MSG =
$$\frac{S_{21}}{S_{12}}$$

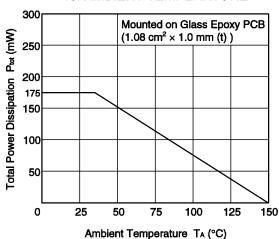
hfe CLASSIFICATION

<R>

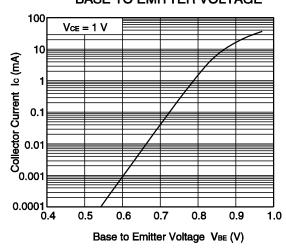
Rank	FB/YFB		
Marking	zF		
h _{FE} Value	130 to 260		

<R> TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

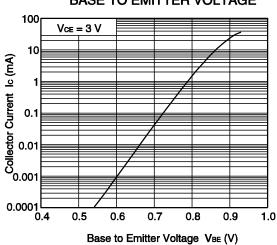




COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

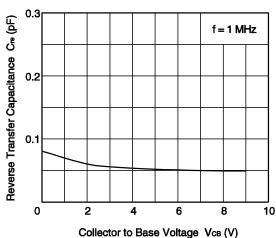


COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

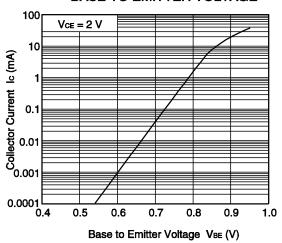


Remark The graphs indicate nominal characteristics.

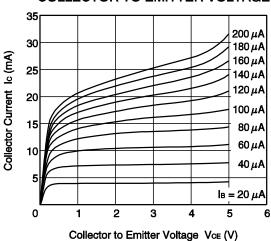
REVERSE TRANSFER CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE

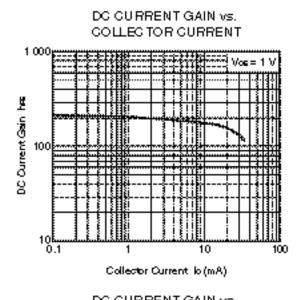


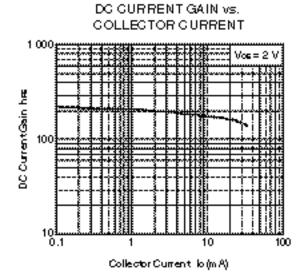
COLLECTOR CURRENT vs. BASE TO EMITTER VOLTAGE

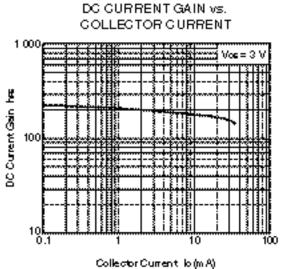


COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE

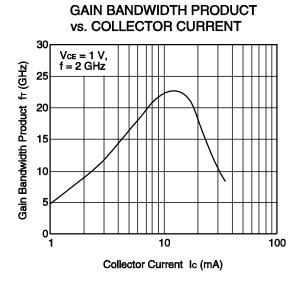


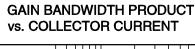


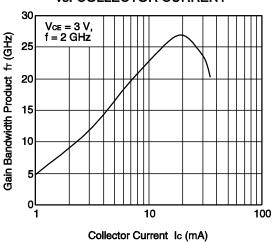




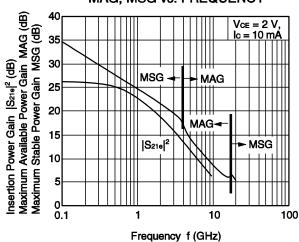
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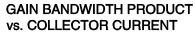


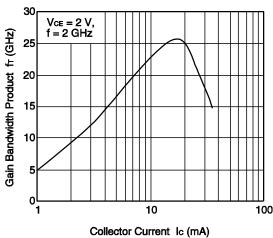


INSERTION POWER GAIN, MAG, MSG vs. FREQUENCY

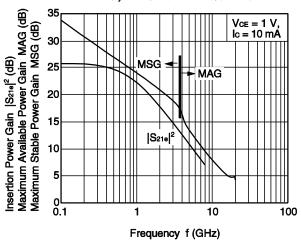


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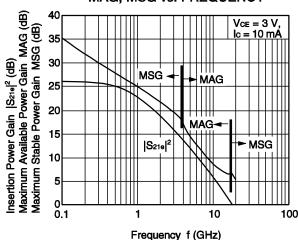


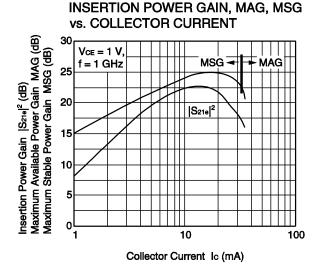


INSERTION POWER GAIN, MAG, MSG vs. FREQUENCY

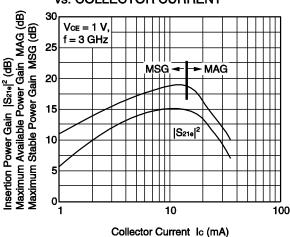


INSERTION POWER GAIN, MAG, MSG vs. FREQUENCY

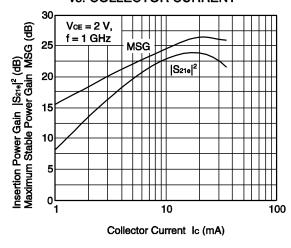






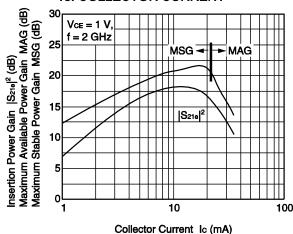


INSERTION POWER GAIN, MSG vs. COLLECTOR CURRENT

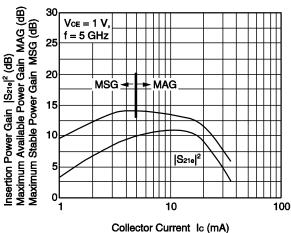


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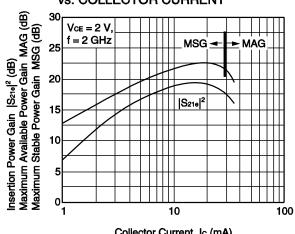
INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



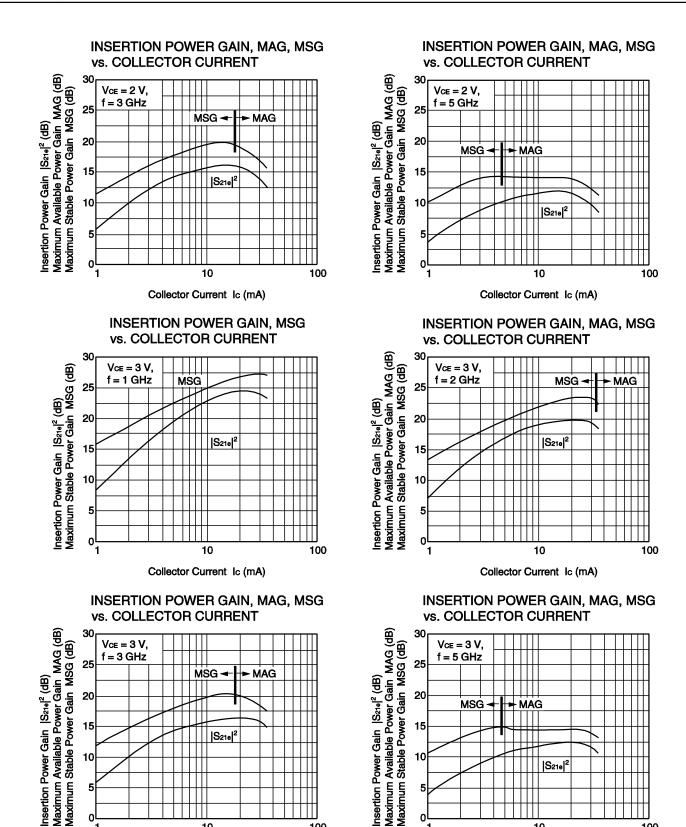
INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



INSERTION POWER GAIN, MAG, MSG vs. COLLECTOR CURRENT



Collector Current Ic (mA)



Remark The graphs indicate nominal characteristics.

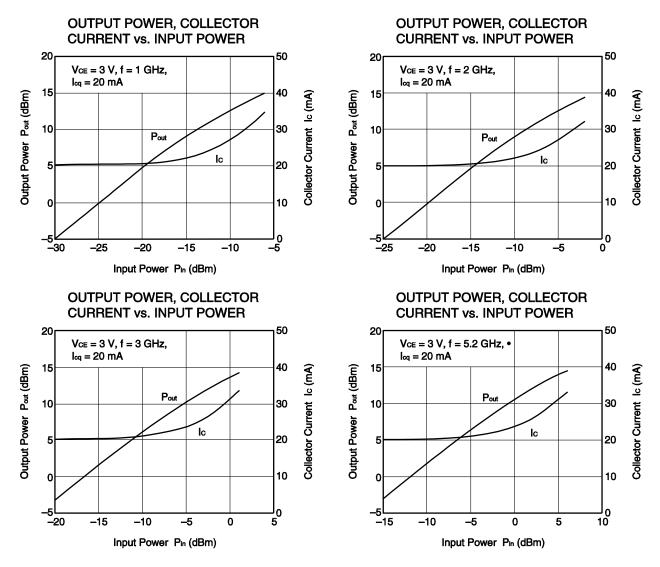
10

Collector Current Ic (mA)

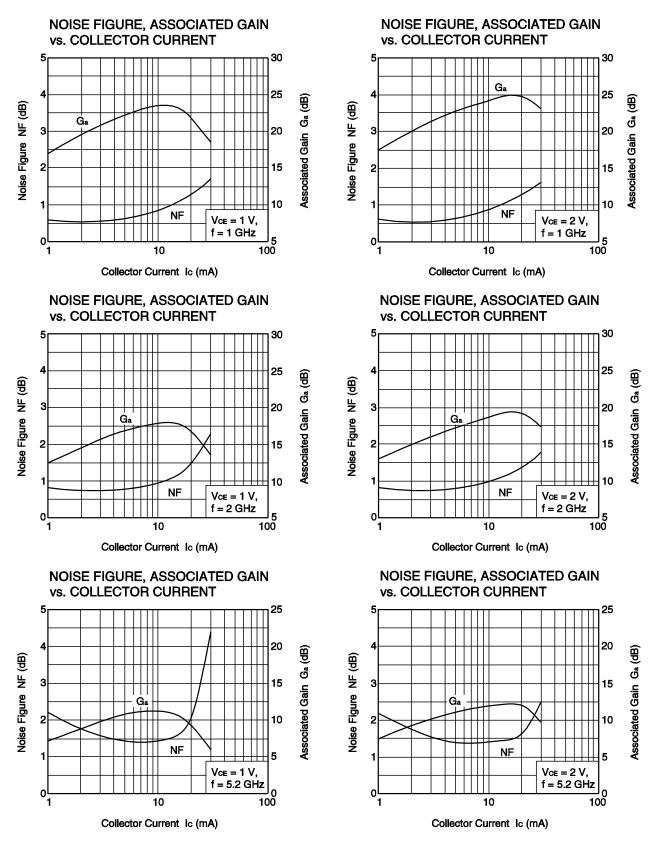
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Collector Current Ic (mA)

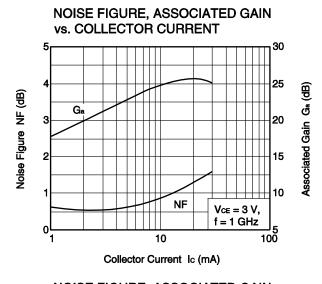
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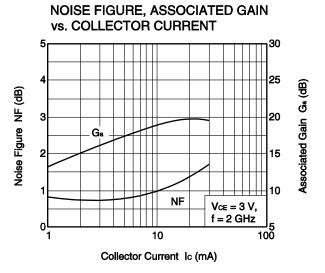


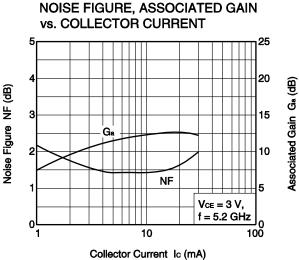
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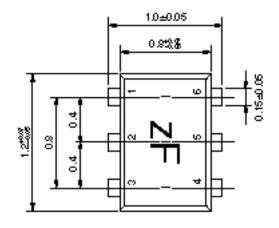
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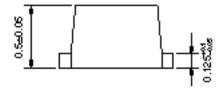
<R> S-PARAMETERS

- S-parameters and noise parameters are provided on our Web site in a format (S2P) that enables the direct import of the parameters to microwave circuit simulators without the need for keyboard inputs.
- · Click here to download S-parameters.
- [RF and Microwave] ® [Device Parameters]
- · URL http://www.necel.com/microwave/en/

PACKAGE DIMENSIONS

6-PIN LEAD-LESS MINIMOLD (M16, 1208 PKG) (UNIT: mm)





PIN CONNECTIONS

- 1. Collector
- 2. Emitter
- 3. Emitter
- 4. Base
- 5. Emitter
- 6. Emitter

Caution All four Emitter-pins should be connected to PWB in order to obtain better Electrical performance and heat sinking.